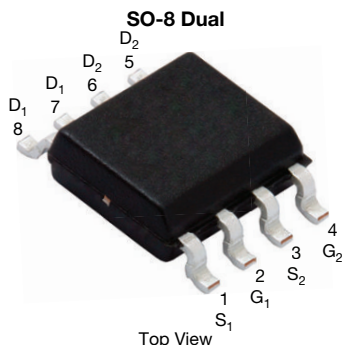


Automotive Dual N-Channel 30 V (D-S) 175 °C MOSFET

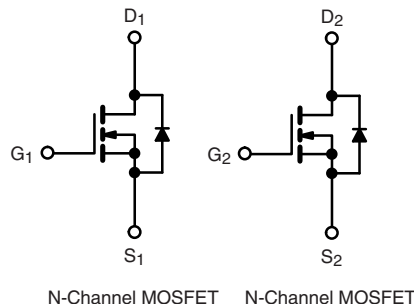


FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0123
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0135
I_D (A)	8
Configuration	Dual

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4282CEY (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	30	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	$T_C = 25$ °C ^a	I_D	8	A
	$T_C = 125$ °C		8	
Continuous source current (diode conduction)		I_S	3.5	
Pulsed drain current ^a		I_{DM}	32	
Single pulse avalanche current		I_{AS}	34	
Single pulse avalanche energy		E_{AS}	58	mJ
Maximum power dissipation	$T_C = 25$ °C	P_D	3.9	W
	$T_C = 125$ °C		1.3	
Operating junction and storage temperature range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R_{thJA}	120	°C/W
Junction-to-foot (drain)		R_{thJF}	38	

Notes

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
b. When mounted on 1" square PCB (FR-4 material)



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		30	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.0100	0.0123	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0176	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0210	
		V _{GS} = 4.5 V	I _D = 14 A	-	0.0110	0.0135	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		-	67	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 15 V, f = 1 MHz	-	2125	2700	pF
Output capacitance	C _{OSS}			-	384	495	
Reverse transfer capacitance	C _{rss}			-	111	173	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 15 V, I _D = 11 A	-	31	47	nC
Gate-source charge ^c	Q _{gs}			-	6.7	-	
Gate-drain charge ^c	Q _{gd}			-	4	-	
Gate resistance	R _g	f = 1 MHz		2.45	4.91	7.5	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 1.67 Ω I _D ≅ 9 A, V _{GEN} = 10 V, R _g = 1 Ω		-	11	15	ns
Rise time ^c	t _r			-	4	17	
Turn-off delay time ^c	t _{d(off)}			-	31	51	
Fall ime ^c	t _f			-	4	12	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	32	A
Forward voltage	V _{SD}	I _F = 8 A, V _{GS} = 0 V		-	0.76	1.2	V

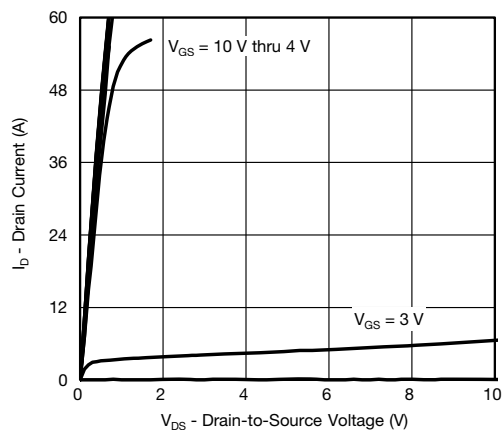
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

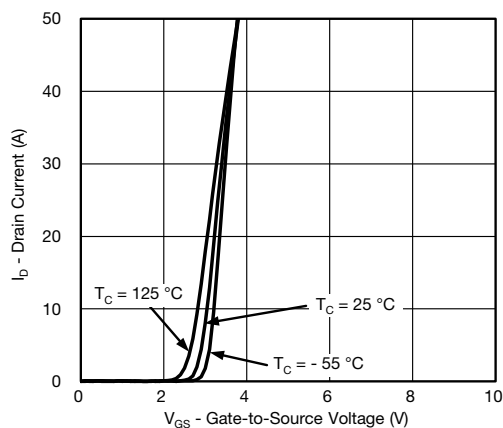
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



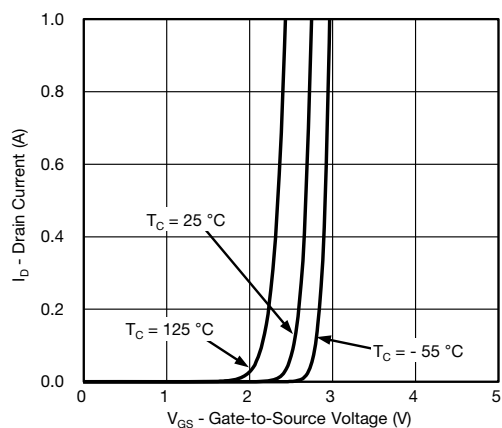
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



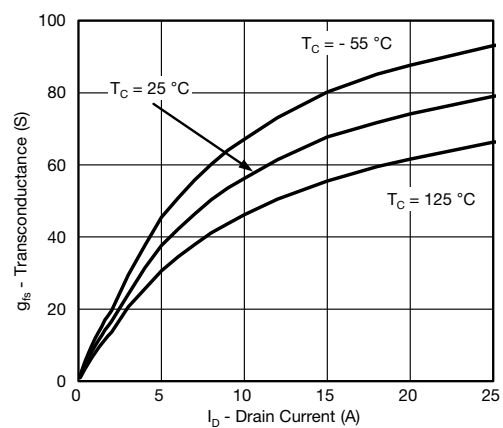
Output Characteristics



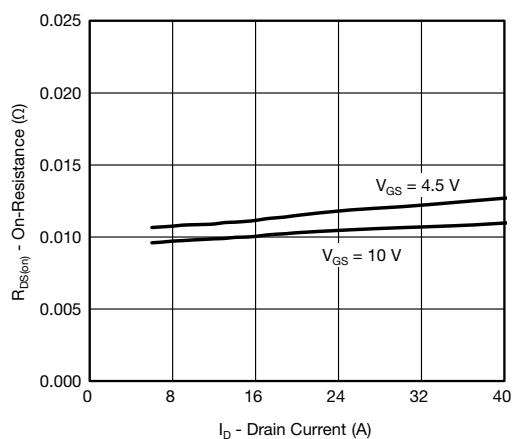
Transfer Characteristics



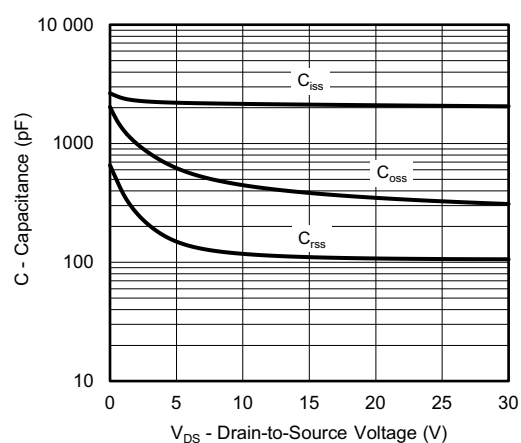
Transfer Characteristics



Transconductance



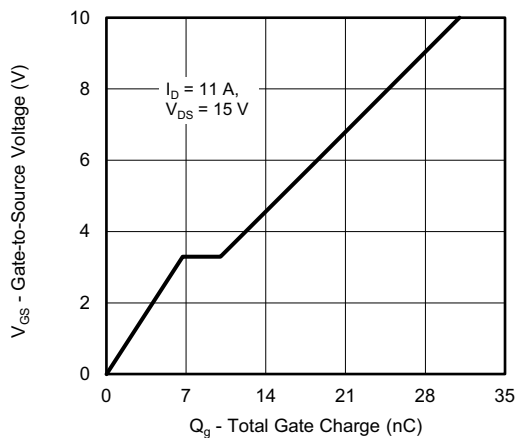
On-Resistance vs. Drain Current



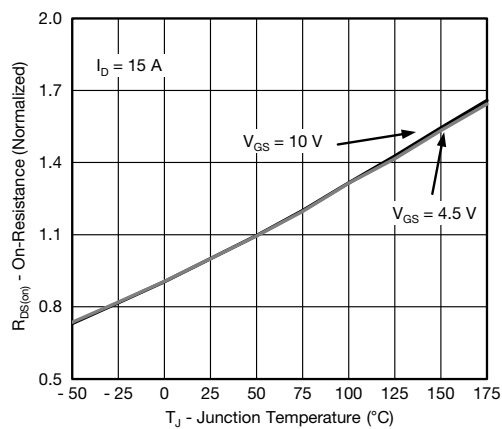
Capacitance



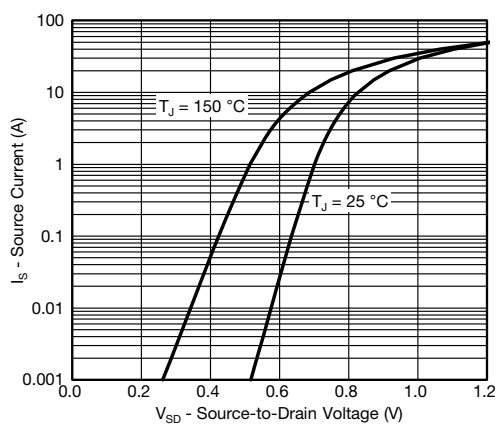
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



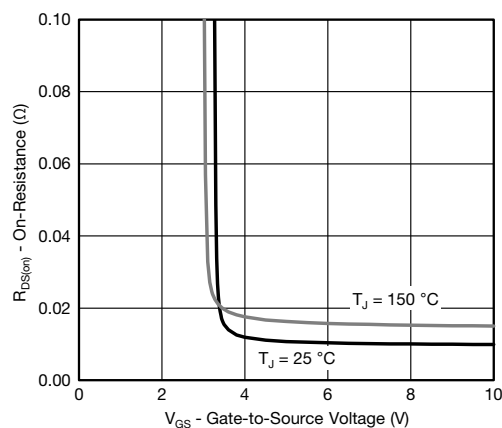
Gate Charge



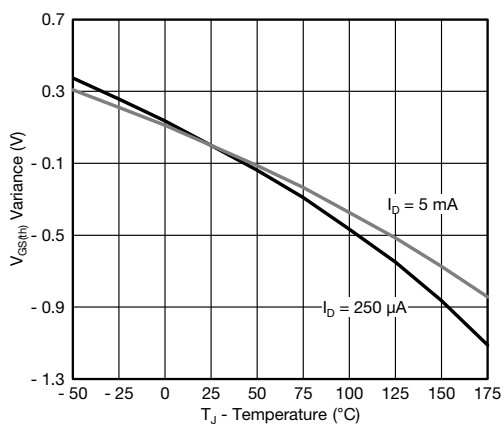
On-Resistance vs. Junction Temperature



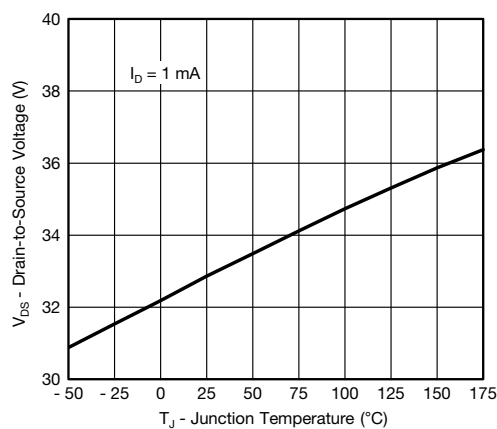
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

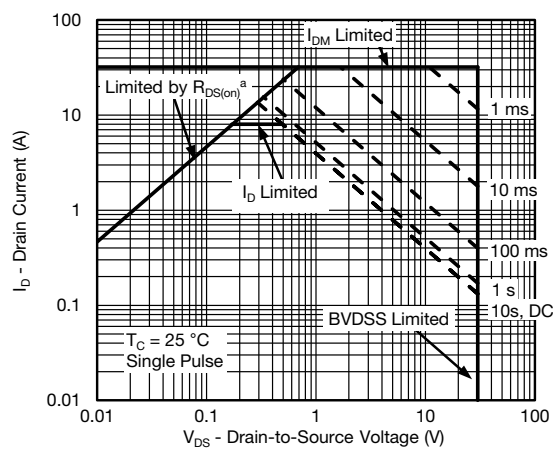


Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

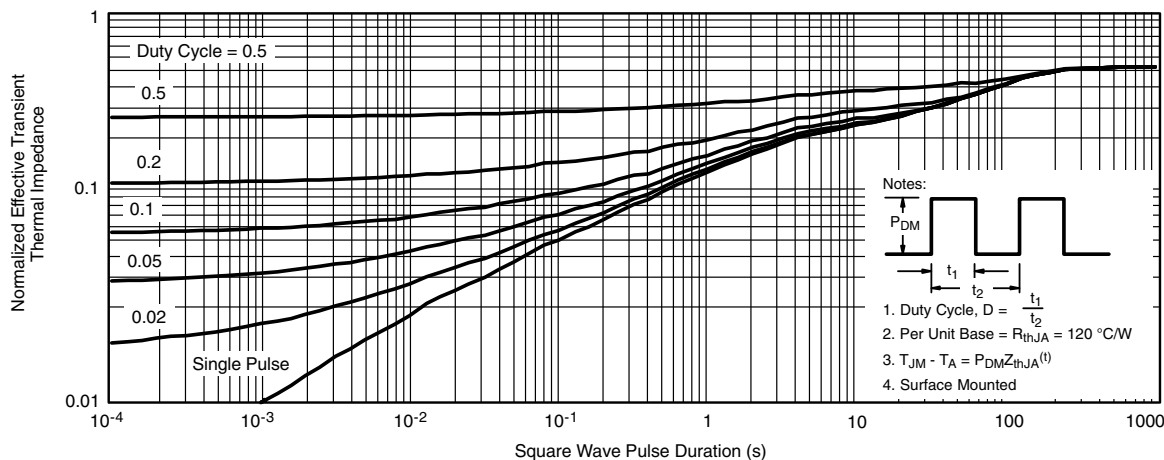
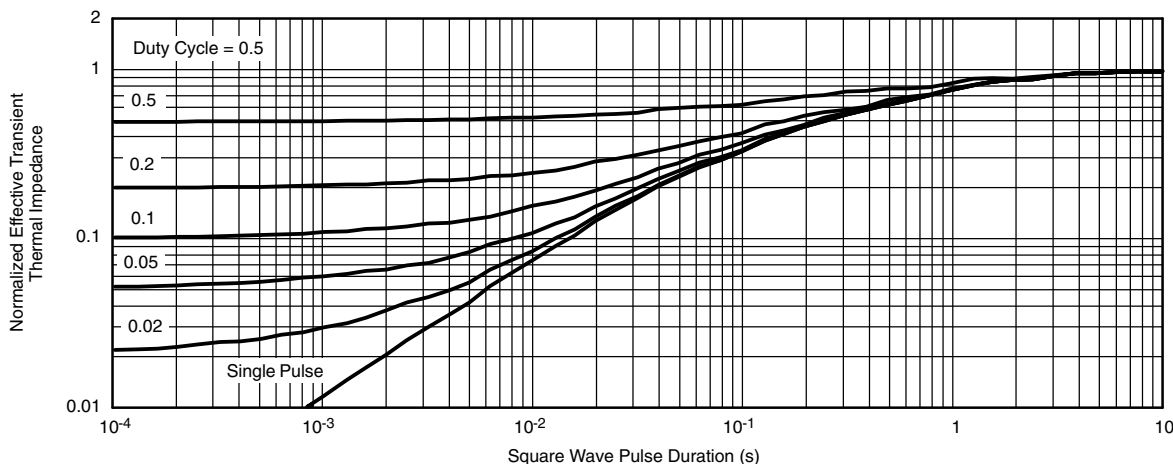
THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

Note

a. $V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$

**THERMAL RATINGS** ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot****Note**

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?61665.

SOIC (NARROW): 8-LEAD

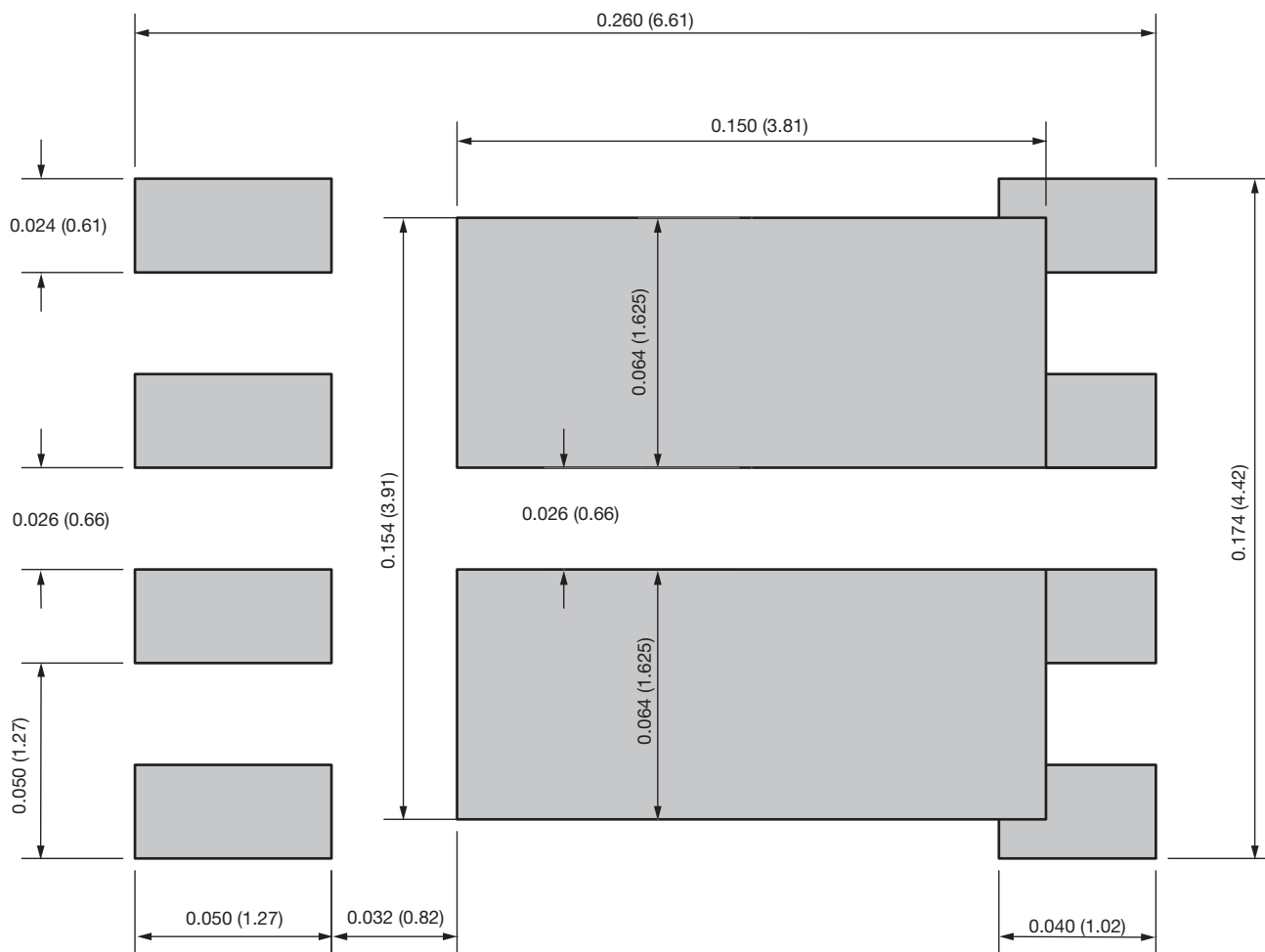
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				



Recommended Land Pattern PowerPAK® SO-8 Dual



Note

- Dimensions in inches (millimeters)

ECN: S24-0458-Rev. A, 06-May-2024
DWG: 3026



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